

Vishay Siliconix

## N-Channel 8-V (D-S) MOSFET

PRODUCT SUMMARY					
V <sub>DS</sub> (V)	R <sub>DS(on)</sub> (Ω)	I <sub>D</sub> (A) <sup>a</sup>	Q <sub>g</sub> (Typ.)		
8	0.011 at V <sub>GS</sub> = 4.5 V	12			
	0.013 at V <sub>GS</sub> = 2.5 V	12			
	0.016 at V <sub>GS</sub> = 1.8 V	12	19 nC		
	0.022 at V <sub>GS</sub> = 1.5 V	12			
	0.041 at V <sub>GS</sub> = 1.2 V	12			

#### **FEATURES**

- TrenchFET<sup>®</sup> Power MOSFET
- New Thermally Enhanced PowerPAK<sup>®</sup> SC-70 Package
- Small Footprint Area Material categorization:
- For definitions of compliance please see www.vishay.com/doc?99912

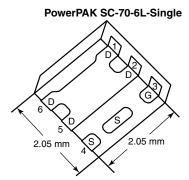
#### **APPLICATIONS**

Load Switch for Portable Applications

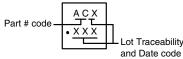


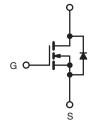
RoHS COMPLIANT HALOGEN

FREE



#### Marking Code





**Ordering Information:** 

SiA414DJ-T4-GE3 (Lead (Pb)-free and Halogen-free) SiA414DJ-T1-GE3 (Lead (Pb)-free and Halogen-free)

N-Channel MOSFET

D

Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V <sub>DS</sub>	8	V	
Gate-Source Voltage		V <sub>GS</sub>	± 5	V	
Continuous Drain Current (T <sub>J</sub> = 150 °C)	$T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{A} = 25 \text{ °C}$	I <sub>D</sub>	12 <sup>a</sup> 12 <sup>a</sup> 12 <sup>a, b, c</sup>		
T <sub>A</sub> = 70 °C   Pulsed Drain Current		I <sub>DM</sub>	<u>11.6<sup>b, c</sup></u> 40	A	
Continuous Source-Drain Diode Current	T <sub>C</sub> = 25 °C T <sub>A</sub> = 25 °C	I <sub>S</sub>	12 <sup>a</sup> 2.9 <sup>b, c</sup>		
Maximum Power Dissipation	$T_{C} = 25 \text{ °C}$ $T_{C} = 70 \text{ °C}$ $T_{C} = 25 \text{ °C}$	- P <sub>D</sub> -	19 12	w	
	$T_{A} = 25 \text{ °C}$ $T_{A} = 70 \text{ °C}$	-	3.5 <sup>b, c</sup> 2.2 <sup>b, c</sup>		
Operating Junction and Storage Temperature Range Soldering Recommendations (Peak Temperature) <sup>d, e</sup>		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 150 260	°C	

#### THEDMAL DEGISTANCE DATINGS

Parameter		Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient <sup>b, f</sup>	t ≤ 5 s	R <sub>thJA</sub>	28	36	°C/W	
Maximum Junction-to-Case (Drain)	Steady State	R <sub>thJC</sub>	5.3	6.5	0/10	

Notes:

a. Package limited

b. Surface mounted on 1" x 1" FR4 board.

c. t = 5 s.

- d. See solder profile (<u>www.vishay.com/ppg273257</u>). The PowerPAK SC-70 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
   e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.

Maximum under steady state conditions is 80 °C/W. f.

# SiA414DJ

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static	•				•		
Drain-Source Breakdown Voltage	V <sub>DS</sub>	$V_{GS} = 0 V, I_{D} = 250 \mu A$	8			V	
V <sub>DS</sub> Temperature Coefficient	$\Delta V_{DS}/T_{J}$	L 050 vA		9		mV/°C	
V <sub>GS(th)</sub> Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	l <sub>D</sub> = 250 μA		- 3			
Gate-Source Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}$ , $I_D = 250 \ \mu A$	0.35		0.8	V	
Gate-Source Leakage	I <sub>GSS</sub>	$V_{DS} = 0 V, V_{GS} = \pm 5 V$			± 100	nA	
	I <sub>DSS</sub>	$V_{DS} = 8 V, V_{GS} = 0 V$			1	μΑ	
Zero Gate Voltage Drain Current		$V_{DS} = 8 V, V_{GS} = 0 V, T_{J} = 55 °C$			10		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 4.5 \text{ V}$	20			Α	
		V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 9.7 A		0.009	0.011	-	
		V <sub>GS</sub> =2.5 V, I <sub>D</sub> =9 A		0.011	0.013		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 8.1 A		0.013	0.016	Ω	
		V <sub>GS</sub> = 1.5 V, I <sub>D</sub> = 4.5 A		0.016	0.022	-	
		V <sub>GS</sub> = 1.2 V, I <sub>D</sub> = 2.4 A		0.027	0.041		
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	$V_{DS} = 4 V, I_{D} = 9.7 A$		50		S	
Dynamic <sup>b</sup>						1	
Input Capacitance	C <sub>iss</sub>			1800		pF	
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = 4 V, V <sub>GS</sub> = 0 V, f = 1 MHz		650			
Reverse Transfer Capacitance	C <sub>rss</sub>			450			
		$V_{DS} = 4 V, V_{GS} = 5 V, I_{D} = 10 A$		21	32	nC	
Total Gate Charge	Qg			19	29		
Gate-Source Charge	Q <sub>gs</sub>	$V_{DS} = 4 \text{ V}, V_{GS} = 4.5 \text{ V}, I_D = 10 \text{ A}$		2.5			
Gate-Drain Charge	Q <sub>gd</sub>			6.5			
Gate Resistance	Rg	f = 1 MHz		2.5		Ω	
Turn-on Delay Time	t <sub>d(on)</sub>			12	20		
Rise Time	t <sub>r</sub>	$V_{DD} = 4 V, R_{L} = 0.4 \Omega$		10	15	- ns	
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD} = 4.0$ , $H_L = 0.4.22$ $I_D \cong 10$ A, $V_{GEN} = 4.5$ V, $R_q = 1 \Omega$		65	100		
Fall Time	t <sub>f</sub>			20	30		
Turn-on Delay Time	t <sub>d(on)</sub>			10	15		
Rise Time	t <sub>r</sub>	$V_{DD} = 4 V, R_1 = 0.4 \Omega$		10	15		
Turn-Off Delay Time	t <sub>d(off)</sub>	$V_{DD} = 4 V, R_L = 0.4 \Omega$ $I_D \cong 10 \text{ A}, V_{GEN} = 5 \text{ V}, R_g = 1 \Omega$		35	55		
Fall Time	t <sub>f</sub>			10	15		
Drain-Source Body Diode Characteristic	S						
Continuous Source-Drain Diode Current	۱ <sub>S</sub>	T <sub>C</sub> = 25 °C			12	A	
Pulse Diode Forward Current	I <sub>SM</sub>				40		
Body Diode Voltage	V <sub>SD</sub>	$I_{S} = 10 \text{ A}, V_{GS} = 0 \text{ V}$		0.8	1.2	V	
Body Diode Reverse Recovery Time	t <sub>rr</sub>			40	80	ns	
Body Diode Reverse Recovery Charge	Q <sub>rr</sub>	I <sub>F</sub> = 10 A, di/dt = 100 A/μs, T <sub>J</sub> = 25 °C		20	40	nC	
Reverse Recovery Fall Time	t <sub>a</sub>			12		ns	
Reverse Recovery Rise Time	t <sub>b</sub>			28			

Notes:

a. Pulse test; pulse width  $\leq$  300  $\mu s,$  duty cycle  $\leq$  2 %

b. Guaranteed by design, not subject to production testing.

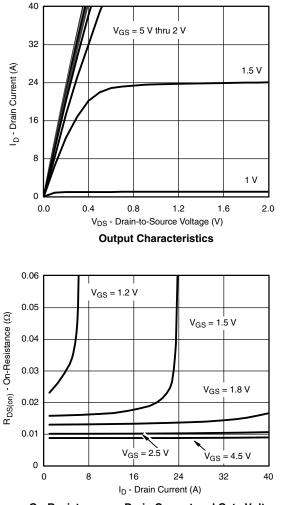
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

www.vishay.com 2 For more information please contact: pmostechsupport@vishay.com

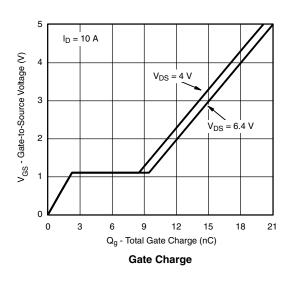
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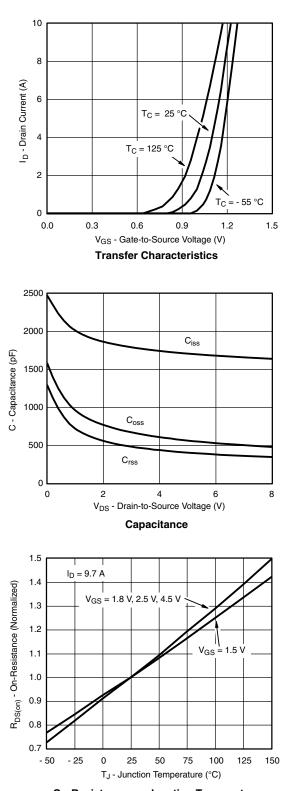


### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



**On-Resistance vs. Drain Current and Gate Voltage** 





**On-Resistance vs. Junction Temperature** 

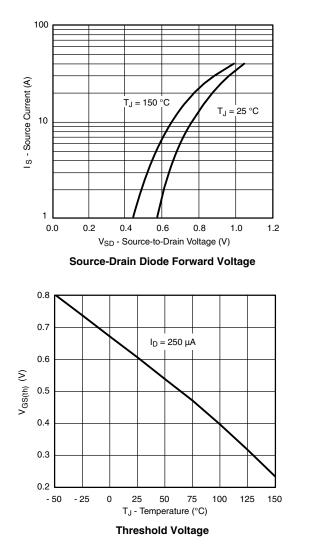
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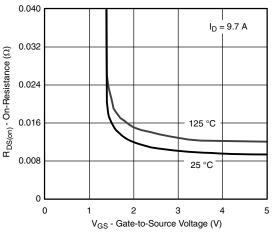
## SiA414DJ



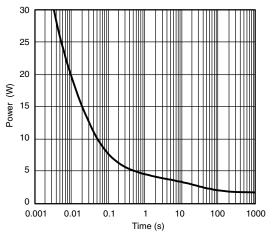
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### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

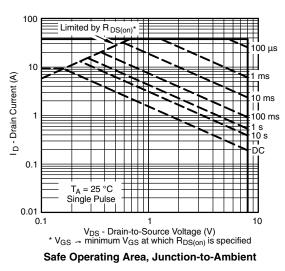




On-Resistance vs. Gate-to-Source Voltage



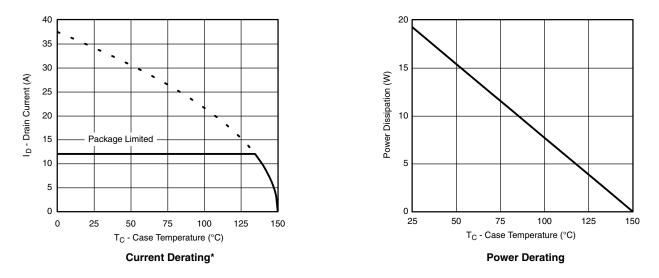
Single Pulse Power (Junction-to-Ambient)



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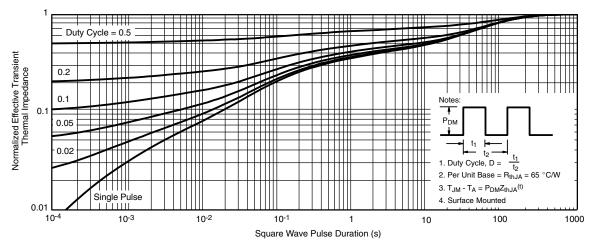
\* The power dissipation  $P_D$  is based on  $T_{J(max)} = 150$  °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

## SiA414DJ

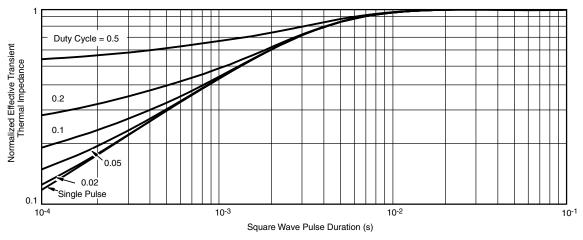


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#### TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see <a href="http://www.vishay.com/ppg773954">www.vishay.com/ppg773954</a>.

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# PowerPAK<sup>®</sup> SC70-6L

VISHA

# b PIN2 PIN1 PIN3 \_ ₹



b

PIN3

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PIN2

PIN1

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<sup>1</sup> 



## RECOMMENDED PAD LAYOUT FOR PowerPAK<sup>®</sup> SC70-6L Single



Dimensions in mm/(Inches)

Return to Index



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